# 2N2907A

# **Small Signal Switching Transistor**

## **PNP Silicon**

#### **Features**

- MIL-PRF-19500/291 Qualified
- Available as JAN, JANTX, and JANTXV

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	-60	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-60	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current – Continuous	Ic	-600	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C	P <sub>T</sub>	500	mW
Total Device Dissipation @ T <sub>C</sub> = 25°C	P <sub>T</sub>	1.0	W
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C

#### THERMAL CHARACTERISTICS

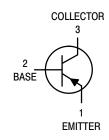
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	325	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	150	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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TO-18 CASE 206AA STYLE 1

#### **ORDERING INFORMATION**

Device	Package	Shipping
JAN2N2907A		
JANTX2N2907A	TO-18	Bulk
JANTXV2N2907A		

#### 2N2907A

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		1		
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = –10 mAdc)	V <sub>(BR)CEO</sub>	-60	_	Vdc
Collector – Emitter Cutoff Current (V <sub>CE</sub> = -50 Vdc)	I <sub>CES</sub>	-	-50	nAdc
Collector–Base Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -60 \text{ Vdc}, I_E = 0)$	Ісво	- -	-10 -10	nAdc μAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = -4.0 Vdc) (V <sub>EB</sub> = -5.0 Vdc)	I <sub>EBO</sub>	- -	-50 -10	nAdc μAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain $ \begin{array}{l} (I_C = -0.1 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -1.0 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -1.0 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -150 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -500 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -500 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \end{array} $	h <sub>FE</sub>	75 100 100 100 50	- 450 - 300 -	-
Collector – Emitter Saturation Voltage ( $I_C = -150 \text{ mAdc}$ , $I_B = -15 \text{ mAdc}$ ) ( $I_C = -500 \text{ mAdc}$ , $I_B = -50 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	- -	-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage ( $I_C = -150 \text{ mAdc}$ , $I_B = -15 \text{ mAdc}$ ) ( $I_C = -500 \text{ mAdc}$ , $I_B = -50 \text{ mAdc}$ )	V <sub>BE(sat)</sub>	-0.6 -	-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS	•	•		
Magnitude of Small–Signal Current Gain ( $I_C = -20 \text{ mAdc}$ , $V_{CE} = -20 \text{ Vdc}$ , $f = 100 \text{ MHz}$ )	h <sub>fe</sub>	2.0	_	_
Small–Signal Current Gain ( $I_C = -1.0 \text{ mAdc}$ , $V_{CE} = -10 \text{ Vdc}$ , $f = 1 \text{ kHz}$ )	h <sub>fe</sub>	100	-	-
Output Capacitance $(V_{CB} = -10 \text{ Vdc}, I_E = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz})$	C <sub>obo</sub>	_	8.0	pF
Input Capacitance $(V_{EB}=-2.0\ Vdc,\ I_{C}=0,\ 100\ kHz \le f \le 1.0\ MHz)$	C <sub>ibo</sub>	_	30	pF
SWITCHING CHARACTERISTICS				
Turn-On Time (Reference Figure in MIL-PRF-19500/291)	t <sub>on</sub>	_	45	ns
Turn-Off Time (Reference Figure in MIL-PRF-19500/291)	t <sub>off</sub>	_	300	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width =  $300 \mu s$ , Duty Cycle  $\leq 2.0\%$ .

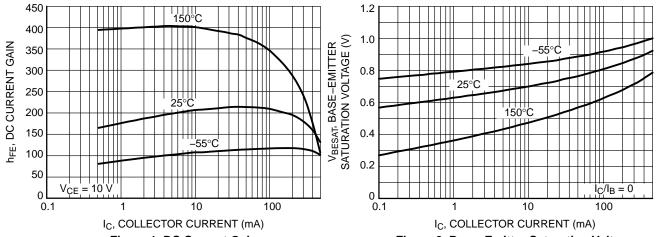


Figure 1. DC Current Gain



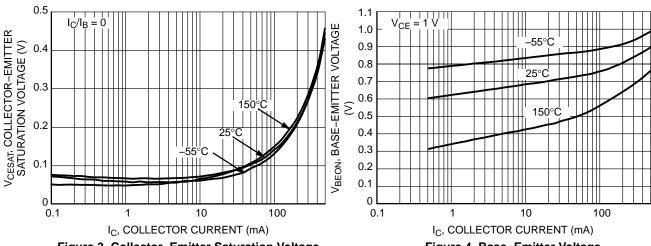


Figure 3. Collector-Emitter Saturation Voltage

Figure 4. Base-Emitter Voltage

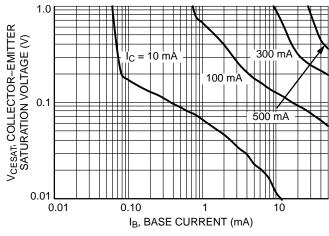


Figure 5. Collector Saturation Region

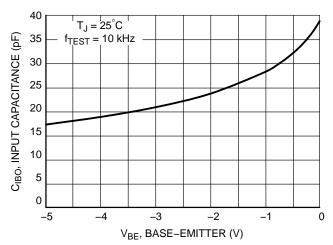


Figure 6. Input Capacitance

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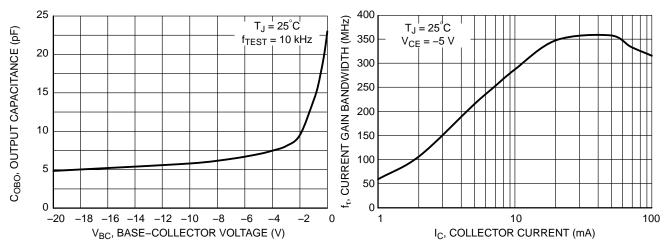


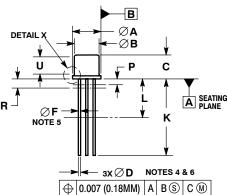
Figure 7. Output Capacitance

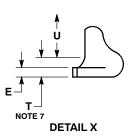
Figure 8. Current Gain Bandwidth Product



TO-18 CASE 206AA **ISSUE A** 

**DATE 21 AUG 2012** 







LEAD IDENTIFICATION

DETAIL

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES.

- DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
  LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE PLANE DEFINED BY DIMENSION R.
  DIMENSION F APPLIES BETWEEN DIMENSION P AND L.
- DIMENSION D APPLIES BETWEEN DIMENSION L AND K.
- BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMENSIONS A, B, AND T.

			INCHES	
	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	5.31	5.84	0.209	0.230
В	4.52	4.95	0.178	0.195
С	4.32	5.33	0.170	0.210
D	0.41	0.53	0.016	0.021
Е		0.76		0.030
F	0.41	0.48	0.016	0.019
Н	0.91	1.17	0.036	0.046
J	0.71	1.22	0.028	0.048
K	12.70	19.05	0.500	0.750
L	6.35		0.250	
M	45°BSC		45°	BSC
N	2.54	BSC	0.100 BSC	
Р		1.27		0.050
R	1.37 BSC		0.054	BSC
Т		0.76		0.030
ш	2.54		0.100	

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STYLE 1:	EMITTER
	BASE
_	COLLECTOR
U.	OOLLLOIGI

STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE & CASE

STYLE 7: PIN 1. ANODE 2. BASE 3. CATHODE

STYLE 10: PIN 1. BASE 2. EMITTER 3. BASE

STYLE 2: PIN 1. SOURCE, SUBSTRATE & CASE 2. GATE

3. DRAIN

STYLE 5: PIN 1. EMITTER 2. BASE 1 3 BASE 2

STYLE 8: PIN 1. GATE 2. ANODE 1 3. ANODE 2

STYLE 11:
PIN 1. DRAIN
2. GATE
3. SOURCE, SUBSTRATE

STYLE 3: PIN 1. SOURCE 2. DRAIN 3. GATE

STYLE 6:

PIN 1. CATHODE 2. GATE 3. ANODE

STYLE 9:

PIN 1. ANODE 2 2. ANODE 1 3. GATE (CONNECTED TO CASE)

STYLE 12: PIN 1. SOURCE 2. GATE 3. DRAIN (CASE)

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